

Title (en)
ELECTRON-EMITTING DEVICE

Title (de)
ELEKTRONEN-EMISSIONSVORRICHTUNG

Title (fr)
DISPOSITIF D'ÉMISSION D'ÉLECTRONS

Publication
EP 3531437 A1 20190828 (DE)

Application
EP 18158898 A 20180227

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Abstract (en)
[origin: WO2019166161A1] The invention relates to an electron-emission device, comprising at least one electron emitter (2) having at least one emission surface (3) and at least one barrier grid (5), which is spaced apart from the emission surface (3) of the electron emitter (2) and has a predefinable number of individually controllable grid segments (G1 – G7, GN). According to the invention, a respective at least one individually predefinable grid voltage can be applied at each of the grid segments (G1 – G7, GN). An electron-emission device of this type permits a simple adjustment of the image quality with minimal anode load.

Abstract (de)
Die Erfindung betrifft eine Elektronen-Emissionsvorrichtung, umfassend wenigstens einen Elektronen-Emitter (2) mit wenigstens einer Emissionsfläche (3) und wenigstens ein Sperrgitter (5), das zur Emissionsfläche (3) des Elektronen-Emitters (2) beabstandet ist und eine vorgebbare Anzahl von einzeln ansteuerbaren Gittersegmenten (G- G, G) aufweist. Eine derartige Elektronen-Emissionsvorrichtung erlaubt auf einfache Weise eine Anpassung der Bildqualität bei geringstmöglicher Anodenbelastung.

IPC 8 full level
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Citation (applicant)
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